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[DMG4407SSS-13](#)

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**DMG4407SS**

**P-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = +25^\circ C$
-30V	11mΩ @ $V_{GS} = -20V$	-9.9A
	17mΩ @ $V_{GS} = -6V$	-8.2A

**Description**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

**Features and Benefits**

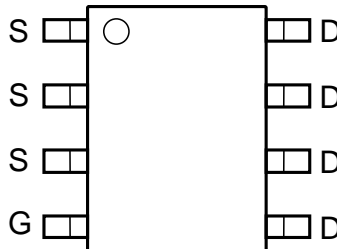
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

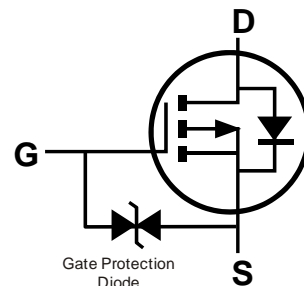
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.075 grams (approximate)



Top View



Top View



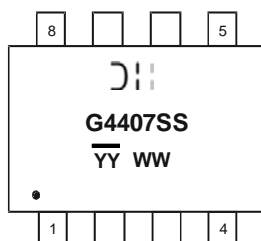
Equivalent Circuit

**Ordering Information** (Note 4)

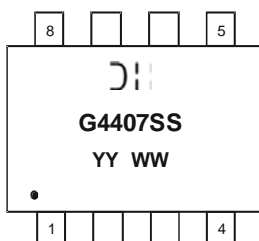
Part Number	Case	Packaging
DMG4407SS-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



Chengdu A/T Site



Shanghai A/T Site

Ⓜ = Manufacturer's Marking  
 G4407SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or Y'Y = Year (ex: 13 = 2013)  
 WW = Week (01 - 53)  
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 Y'Y = Date Code Marking for CAT (Chengdu Assembly/ Test site)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±25	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = -20V	Steady State	I <sub>D</sub>	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	-9.9 -7.9	A
	t < 10s		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	-12.5 -10.0	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = -6V	Steady State	I <sub>D</sub>	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	-8.2 -6.5	A
	t < 10s		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	-11.0 -8.7	A
Maximum Continuous Body Diode Forward Current (Note 6)		I <sub>S</sub>	3.0	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I <sub>DM</sub>	-80	A	

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P <sub>D</sub>	1.45	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	88	°C/W
	t < 10s		50	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.82	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	70	°C/W
	t < 10s		41	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	7.6	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-50 to 155	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.7	—	-3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	9	11	mΩ	V <sub>GS</sub> = -20V, I <sub>D</sub> = 12A
		—	10	13		V <sub>GS</sub> = -10V, I <sub>D</sub> = 10A
		—	12.7	17		V <sub>GS</sub> = -6V, I <sub>D</sub> = 10A
Forward Transfer Admittance	Y <sub>fs</sub>	—	21	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -10A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	2246	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	352	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	294	—	pF	
Gate resistance	R <sub>g</sub>	—	5.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	20.5	—	nC	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -12A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	41	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	8.0	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	11.3	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>L</sub> = 1.25Ω, R <sub>G</sub> = 3Ω,
Turn-On Rise Time	t <sub>r</sub>	—	15.4	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	38.0	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	22.0	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



**DMG4407SSS**

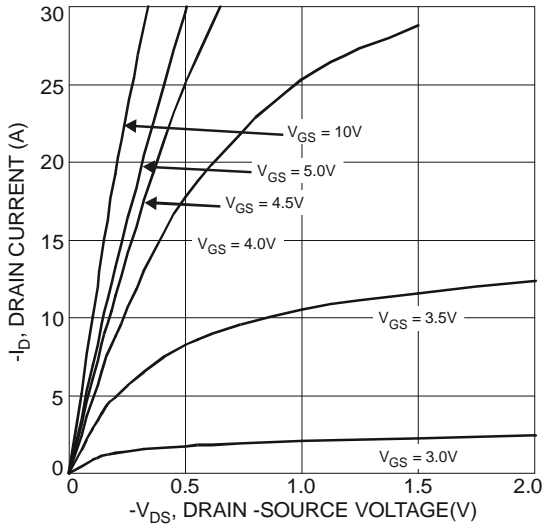


Fig. 1 Typical Output Characteristics

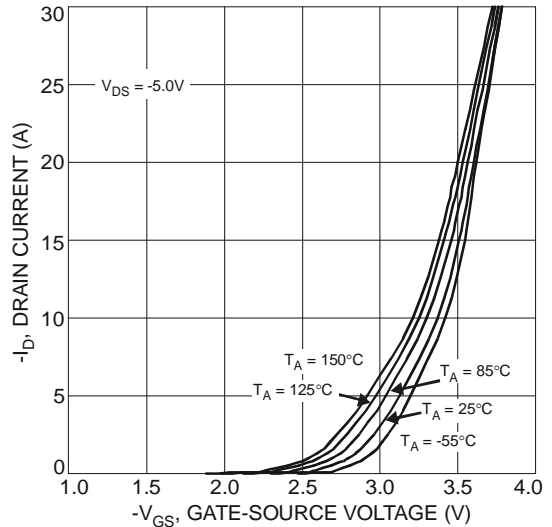


Fig. 2 Typical Transfer Characteristics

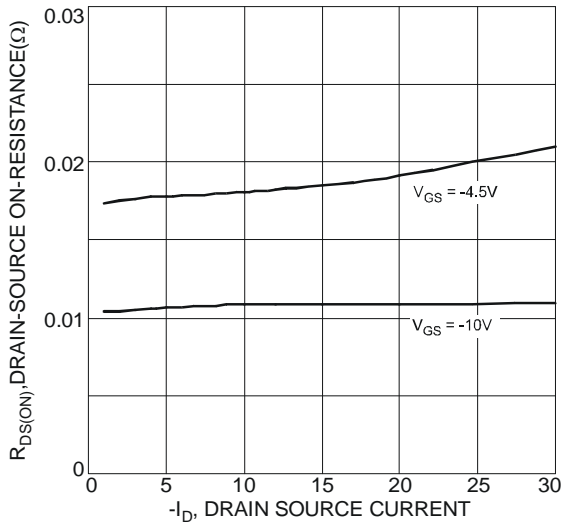


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

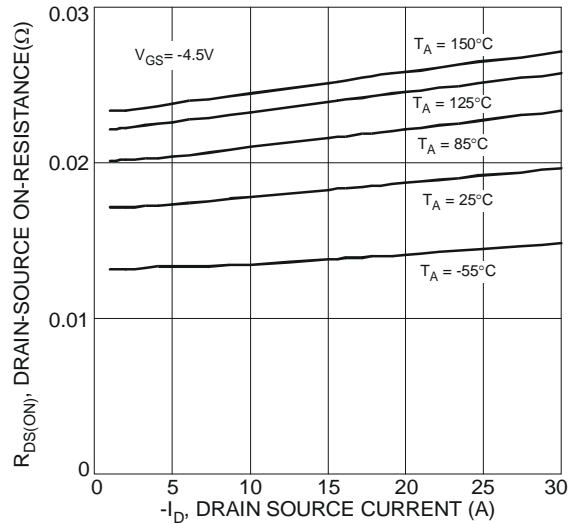


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

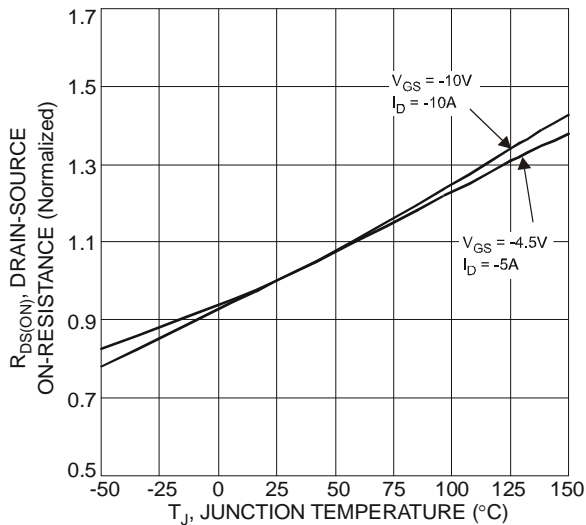


Fig. 5 On-Resistance Variation with Temperature

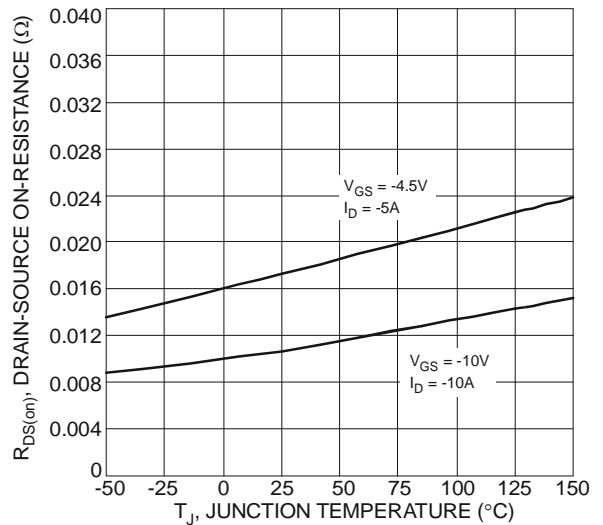


Fig. 6 On-Resistance Variation with Temperature



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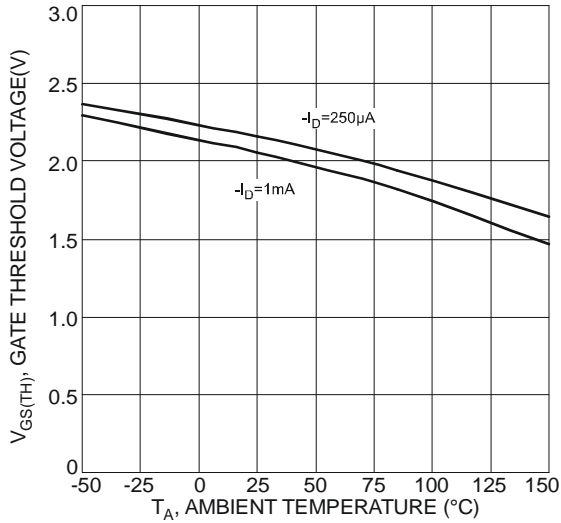


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

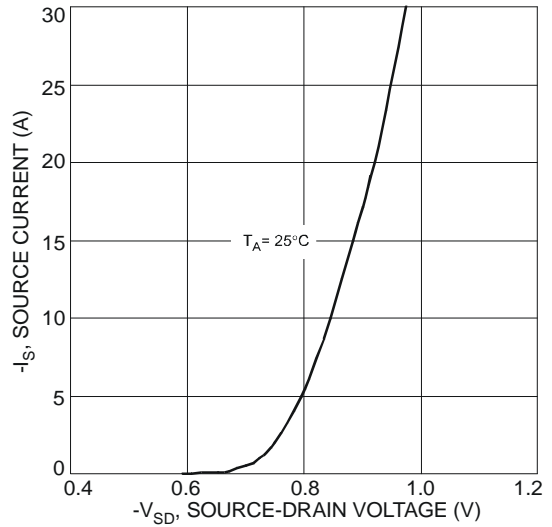


Fig. 8 Diode Forward Voltage vs. Current

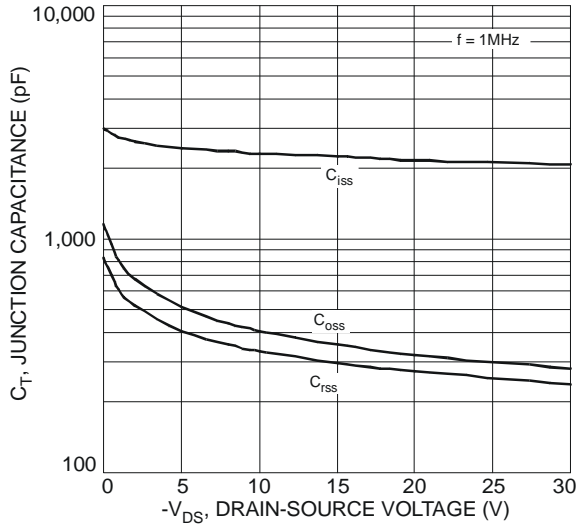


Fig. 9 Typical Junction Capacitance

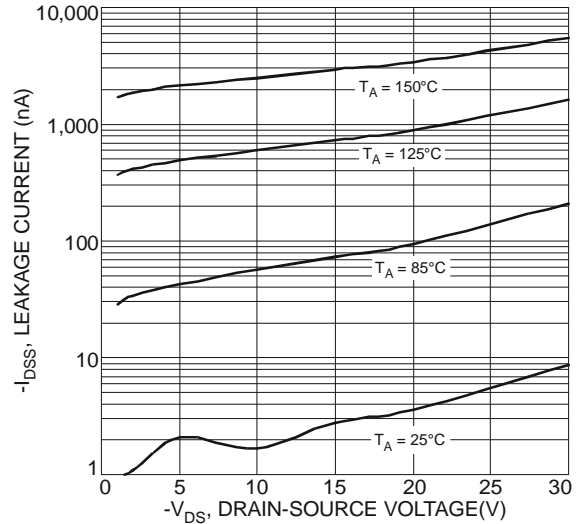


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

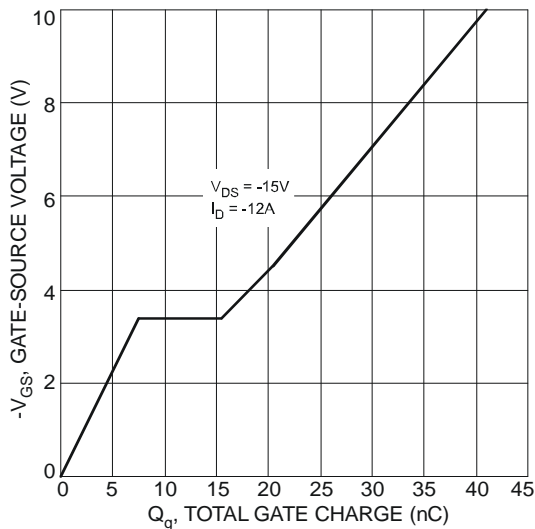


Fig. 11 Gate-Charge Characteristics

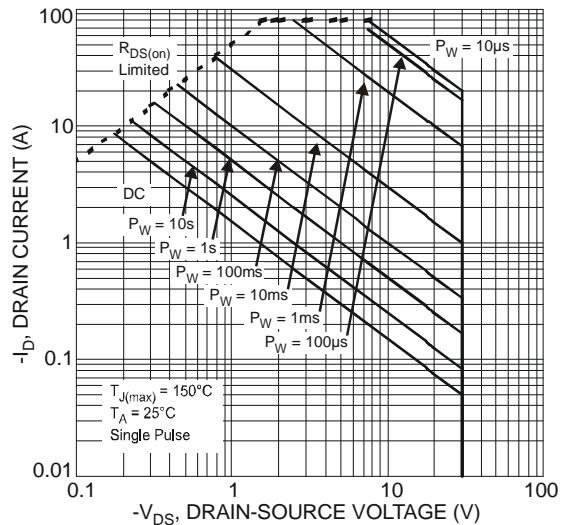
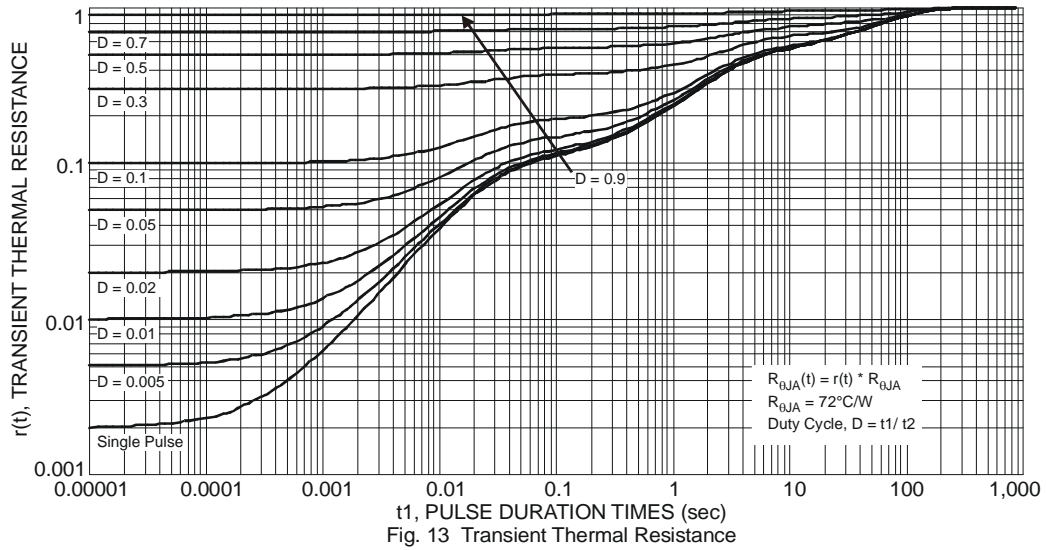
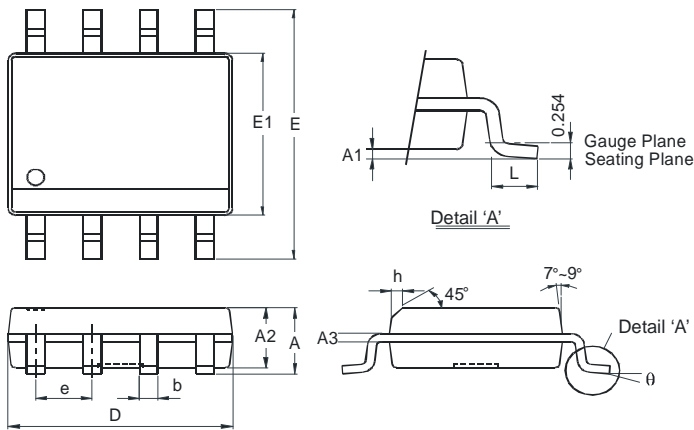


Fig. 12 SOA, Safe Operation Area



**Package Outline Dimensions**

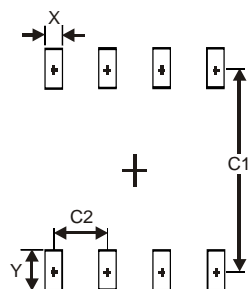
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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